



67,200-447; TSMC 00-0890  
Serial Number 09/975,855

1756  
JFLW

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**TO:** Commissioner for Patents  
PO Box 1450  
Alexandria, VA 22313-1450

**FROM:** Tung & Associates  
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Bloomfield Hills, MI 48302

**DATE:** 8 March 2005

**REF:** Applicant : Hsieh et al. Filing Date : 11 October 2001  
Serial No : 09/975,855 Att'y No. : 67,200-447  
Art Unit : 1756 Examiner : Saleha R Mohamedulla  
Title : Gap Forming Pattern Fracturing Method for Forming Optical  
Proximity Corrected Masking Layer

**AMENDMENT AND RESPONSE TO OFFICE ACTION**

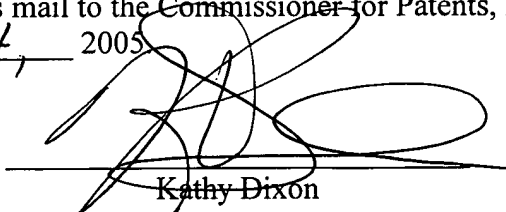
Sir:

In response to an office action mailed 15 December 2004, please consider the following amendments and remarks pertaining to the subject patent application.

There are no amendments to the specification or drawings. Amendments to the claims are contained within a Listing of the Claims that begins on page 2 of this paper. Remarks begin on page 7 of this paper.

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being forwarded in an envelope with sufficient postage as first class mail to the Commissioner for Patents, POB 1450, Alexandria, VA 22313-1450 on Mar. 14, 2005.

  
Kathy Dixon